CHENMKO ENTERPRISE CO.,LTD

CHM9926PAGP

SURFACE MOUNT
N-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 20 Volts CURRENT 26 Ampere

APPLICATION

* Servo motor control.
* Power MOSFET gate drivers.
* Other switching applications.

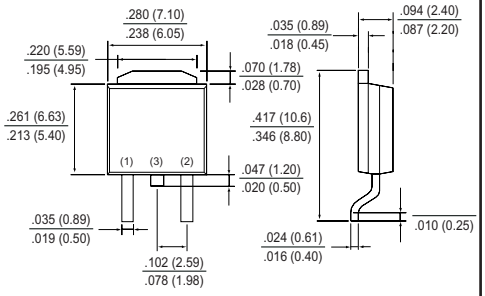
FEATURE

* Small package. (TO-252)
* Super high dense cell design for extremely low $R_{DS(ON)}$.
* High power and current handing capability.

CONSTRUCTION

* N-Channel Enhancement

D-PAK(TO-252)

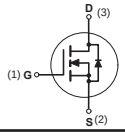


1 Gate
2 Source
3 Drain(Heat Sink)

Dimensions in inches and (millimeters)

TO-252

CIRCUIT



Absolute Maximum Ratings

T_A = 25°C unless otherwise noted

Symbol	Parameter	CHM9926PAGP	Units
V_{DSS}	Drain-Source Voltage	20	V
V_{GSS}	Gate-Source Voltage	±12	V
I_D	Maximum Drain Current - Continuous	26	A
	- Pulsed (Note 3)	78	
P_D	Maximum Power Dissipation at Tc = 25°C	38	W
T_J	Operating Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C

Note : 1. Surface Mounted on FR4 Board , t <=10sec
2. Pulse Test , Pulse width <= 300us , Duty Cycle <= 2%
3. Repetitive Rating , Pulse width linited by maximum junction temperature
4. Guaranteed by design , not subject to production trsting

Thermal characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	50	°C/W

ELECTRICAL CHARACTERISTIC (CHM9926PAGP)

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V			1	µA
I_{GSSF}	Gate-Body Leakage	V_{GS} = 12V, V_{DS} = 0 V			+100	nA
I_{GSSR}	Gate-Body Leakage	V_{GS} = -12V, V_{DS} = 0 V			-100	nA
ON CHARACTERISTICS (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	0.5		1.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=4.5V, I_D=8A			30	mΩ
		V_{GS}=2.5V, I_D=6.6A			40	
g_{FS}	Forward Transconductance	V_{DS} =10V, I_D = 8A		15		S
SWITCHING CHARACTERISTICS (Note 4)						
Q_g	Total Gate Charge	V_{DS}=10V, I_D=8A V_{GS}=4.5V		10	15	nC
Q_{gs}	Gate-Source Charge			2.3		
Q_{gd}	Gate-Drain Charge			2.9		
t_{on}	Turn-On Time	V_{DD}= 10V I_D=1A, V_{GS}= 4.5 V R_{GEN}= 6 Ω		20	40	nS
t_r	Rise Time			18	40	
t_{off}	Turn-Off Time			60	108	
t_f	Fall Time			28	56	
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Drain-Source Diode Forward Current				26	A
V_{SD}	Drain-Source Diode Forward Voltage	I_S = 4A, V_{GS} = 0 V			1.3	V